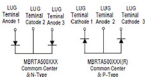


**Silicon Standard  
Recovery Diode**
**MSRTA50060(A) thru  
MSRTA500100(A)**
 $V_{RRM} = 600\text{ V} - 1600\text{ V}$ 
 $I_F = 500\text{ A}$ 
**Features**

- High Surge Capability
- Types up to 1600 V  $V_{RRM}$

**Heavy Three Tower Package**

**Maximum ratings, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	MSRTA50060(A)	MSRTA50080(A)	MSRTA500100(A)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		600	800	1000	V
RMS reverse voltage	$V_{RRMS}$		420	560	700	V
DC blocking voltage	$V_{DC}$		800	800	1000	V
Continuous forward current	$I_F$	$T_C \leq 125\text{ }^\circ\text{C}$	500	500	500	A
Surge non-repetitive forward current, Half Sine Wave	$I_{FSM}$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$	4400	4400	4400	A
Operating temperature	$T_j$		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

**Electrical characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	MSRTA50060(A)	MSRTA50080(A)	MSRTA500100(A)	Unit
Diode forward voltage	$V_F$	$I_F = 500\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$	1.2	1.2	1.2	V
Reverse current	$I_R$	$V_R = 800\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$	25	25	25	$\mu\text{A}$
		$V_R = 600\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	10	10	10	mA

**Thermal characteristics**

Thermal resistance, junction - case	$R_{\theta JC}$		0.12	0.12	0.12	$^\circ\text{C/W}$
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Figure .1- Typical Forward Characteristics

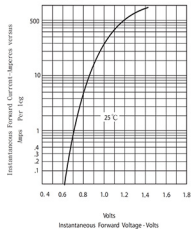


Figure.2 Forward Derating Curve

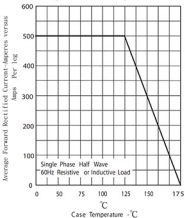


Figure.3-Peak Forward Surge Current

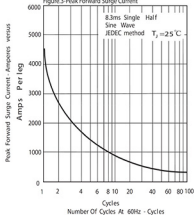


Figure .4-Typical Reverse Characteristics

